

The nature of hypervalent bonding in compounds of pentacoordinated silicon as found from X-ray diffraction and quantum chemical calculations

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On the basis of high-resolution X-ray analysis and quantum chemical calculations the electron density distribution function $\rho(r)$ in the series of silatranes (Fig. 1, *a*) and monochelated compounds with pentacoordinated silicon atom has been studied (Fig. 1, *b* and *c*).

Topological analysis of the $\rho(r)$ has revealed that Si-O and Si-N bonds in silatranes (Fig. 1, *a*) and monochelated compounds with pentacoordinated silicon atom (Fig. 1, *b*) corresponds to interactions of intermediate type in terms of Bader's "Atoms in molecules theory". In the studied silatranes (Fig. 1, *a*) the decreasing of the Si-N distance to 2.0 Å ($X = Cl$) does not lead to weakening of the axial Si-X bond. On the other hand, in the monochelated compounds the decreasing of the Si-O distance to 1.88-1.95 Å causes significant changes in the electron density distribution in the region of the Si-X bonds that does not allow to consider these bonds as "ordinary" covalent ones. The special interest attracts the organosilicon derivatives of salicylamide (Fig. 1, *c*) in which the Si...O interatomic distances falls in the range 2.8 ÷ 3.0 Å that is 0.3 ÷ 0.5 Å less than the sum of the van-der-waals radii of silicon and oxygen atoms. Besides, the Si-X bonds is elongated in comparison to its standart values. So, one may expect the presence of Si...O intramolecular interactions in the above mentioned compounds. However, topological analysis of the $\rho(r)$ has shown the absense of Si...O interaction. The high value of dipole moment (~ 8.3 D) allow one to conclude that elongation of the Si-Cl bond can be explained by its polarization by influence of strong negatively charged OF_2O moiety. This work was supported by the Russian Foundation for Basic Research (grants 03-03-32214 and 02-07-90169).

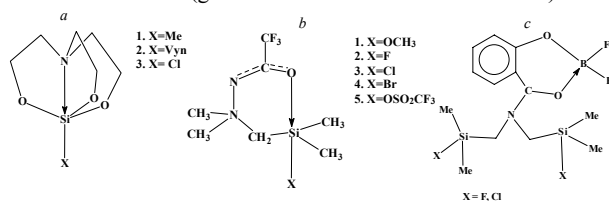


Fig. 1